# Chip Termination <br> 150 Watts, $50 \Omega$ 

## Description

The A150N50X4C is high performance Aluminum Nitride (AIN) chip termination intended as a cost competitive alternative to Beryllium Oxide (BeO). It is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators, and for use in power combiners. The termination is also RoHS compliant!

## General Specifications

| Resistive Element | Thick film |
| :--- | :--- |
| Substrate | AIN Ceramic |
| Terminal Finish | Matte Tin over Nickel Barrier |
| Operating Temperature | -55 to $+150^{\circ} \mathrm{C}$ (see de rating chart) |

Tolerance is $\pm 0.010 "$, unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions in inches.

## Electrical Specifications

| Resistance Value: | 50 Ohms, $\pm 2 \%$ |
| :--- | :--- |
| Power: | 150 Watts |
| Frequency Range: | $\mathrm{DC}-3.0 \mathrm{GHz}$ |
| Return Loss | $>26 \mathrm{~dB}$ |

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. Specifications subject to change.

## Outline Drawing


pg1 of 2

USA/Canada

## Typical Performance:

| A150N50X4C | A150N50X4C |
| :---: | :---: |
|  |  |
| Power Derating: | Suggested Mounting procedures: |
|  <br> *Actual performance could be limited by the solder properties of the application |  |

